

TO-263 Ṁ Ṁ Ł N Ÿ ħ ǻ Z 1

N-CHANNEL MOSFET in a TO-263 Plastic Package.

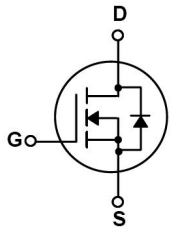
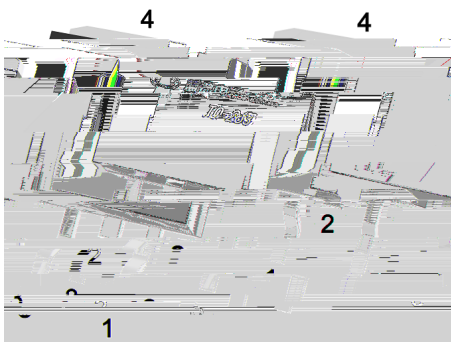
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T L d

These devices are well suited for high efficient switched mode power supplies Active power factor correction, electronic lamp ballast based on half bridge topology, Meet the stringent requirements of automotive applications.

PIN1 $\times$ G

PIN 2 4 x D

PIN 3 x S

/ Marking

♫ M ♪ ♫ " See Marking Instructions.

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蓝箭电子
BLUE ROCKET ELECTRONICS

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Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	120	A
Pulsed Drain Current	I_{DM}	480	A
Gate-Source Voltage	V_{GS}	± 20	V
Single-Pulse Avalanche Energy	E_{AS}	482	mJ
Avalanche Current	I_{AS}	35	A
Total Power Dissipation	$P_D(T_C=25^\circ\text{C})$	187	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	15	$^\circ\text{C/W}$
Steady-State		60	
Thermal Resistance-Junction to Case	$R_{\theta JC}$	0.7	

Parameter	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	44		V
Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 1	nA
Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1	3	V

Static Drain-Source

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/ Electrical Characteristic Curve

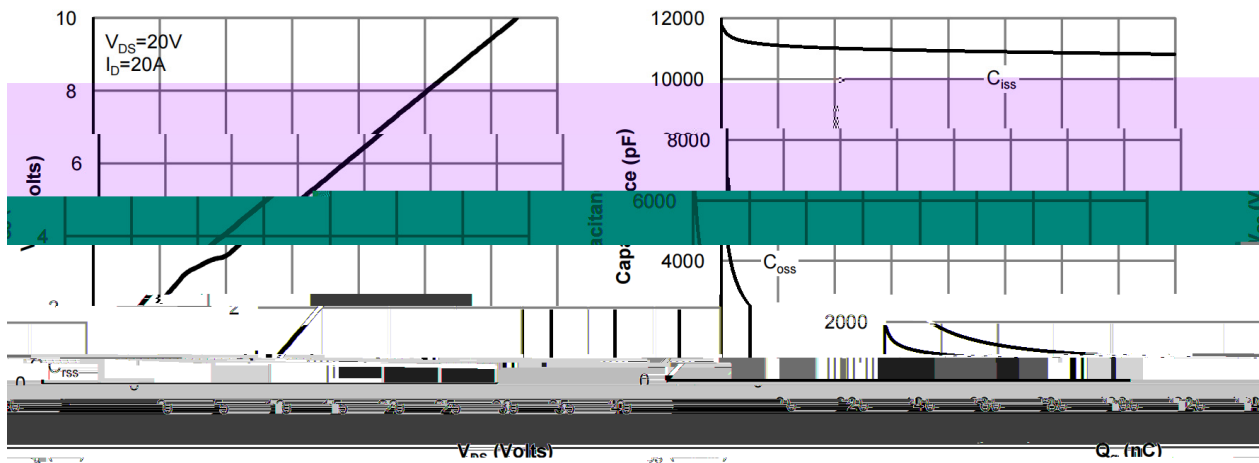
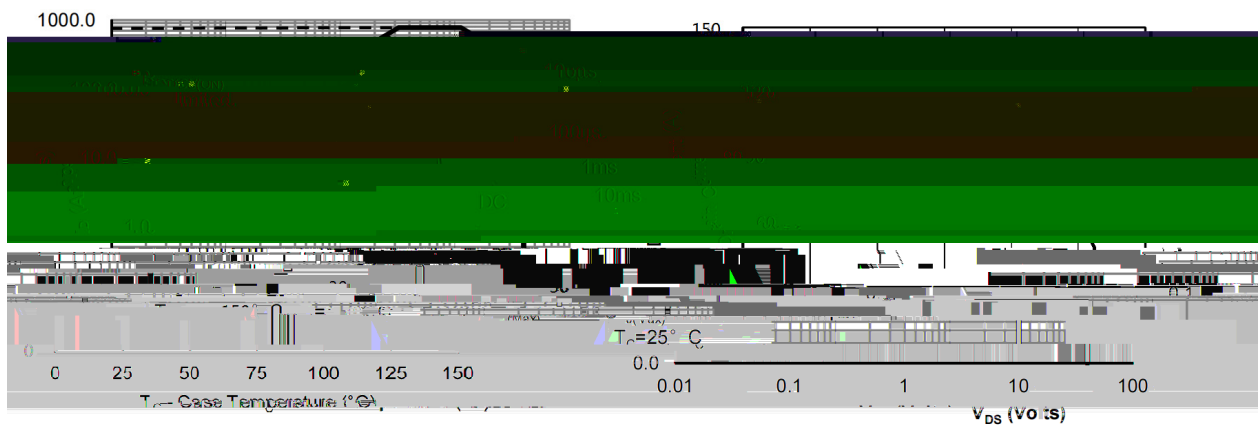
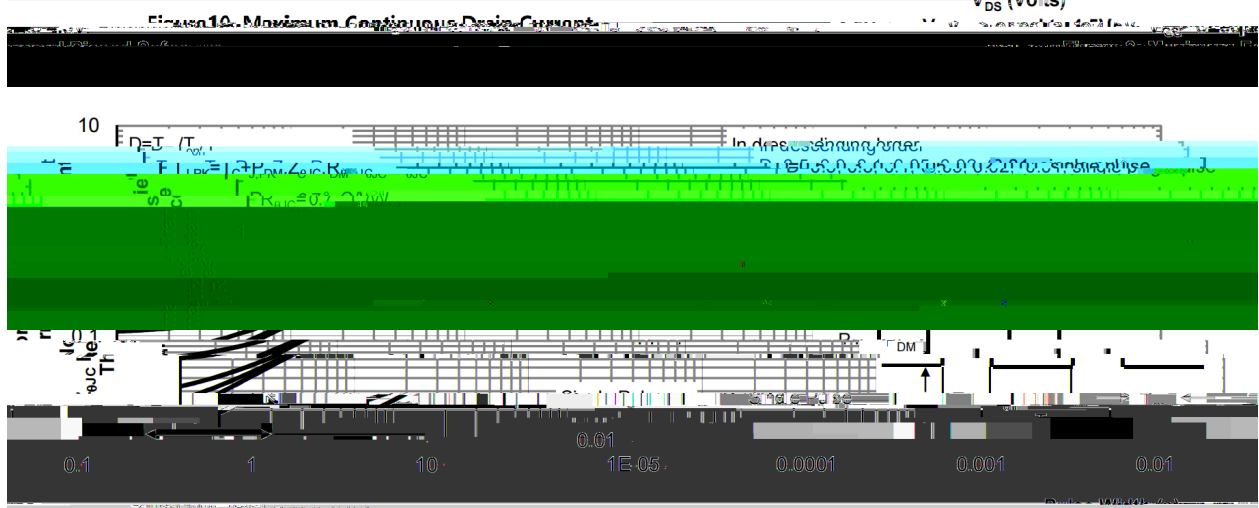
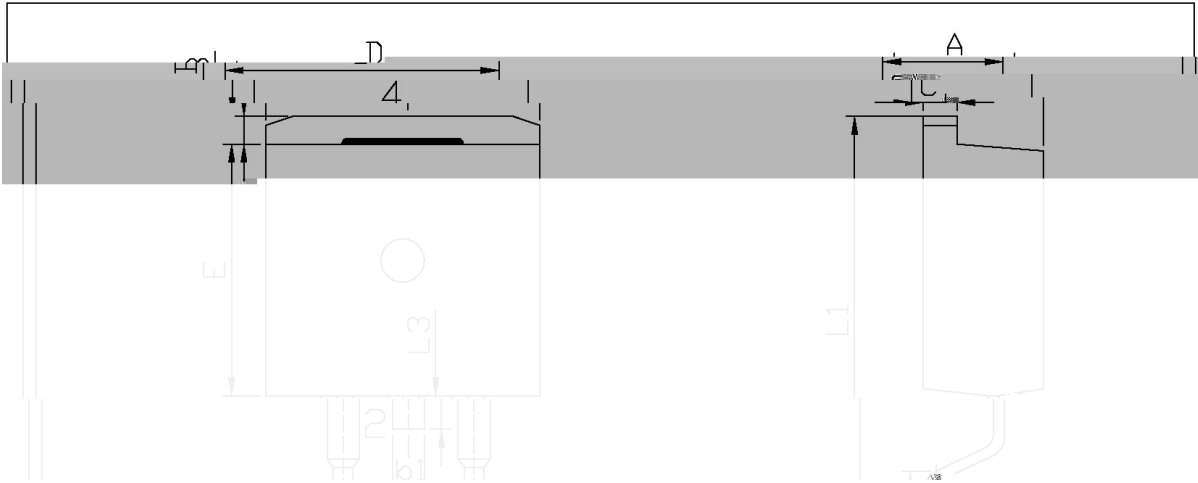


Figure 14: Normalized Maximum Transient Thermal Impedance

/ Package Dimensions



Max	Min	Max	Min
9.40	4.30	4.70	9.00
2.74	1.00	1.40	2.24

15.00	16.00	b1	1.15	1.35	L1
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9.80	10.20
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TP-263

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DATA SHEET

